Kazushige Ueda

List of Publications by Year
in descending order

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122	9,195	50170	38300
papers	citations	46 h-index	95 g-index

127	127	127	6653
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Site-Dependent Tb³⁺ Luminescence by Energy Transfer from Ce³⁺ in Ce³⁺â€“Tb³⁺ Codoped LaLuO₃. Journal of Physical Chemistry C, 2022, 126, 6499-6504.	1.5	6
2	Site-Dependent Eu3+ Photoluminescence in Double Perovskite-Type Alkaline Earth Lanthanum Tantalates. Journal of Luminescence, 2021, 229, 117683.	1.5	14
3	Host Lattice-Excitation-Enhanced Photoluminescence in Eu³⁺-Doped LaInO₃ Epitaxial Films. Crystal Growth and Design, 2021, 21, 2663-2667.	1.4	1
4	Site Dependence of Tb3+ Luminescence in Double Perovskite-Type Alkaline Earth Lanthanum Tantalates. Journal of Physical Chemistry C, 2020, 124, 854-860.	1.5	12
5	Site-Selective Doping and Site-Sensitive Photoluminescence of Eu³⁺ and Tb³⁺ in Perovskite-Type LaLuO₃. Inorganic Chemistry, 2019, 58, 10890-10897.	1.9	40
6	Ultraviolet emission from YAlO3:Gd3+ thin film electroluminescent devices fabricated on perovskite-type oxide substrates. Optical Materials, 2019, 91, 371-375.	1.7	3
7	Ln³⁺ 4f Energy Levels in CaTiO₃ Analyzed by XPS Measurements. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1700776.	0.8	3
8	Luminescence and Location of Gd³⁺ or Tb³⁺ Ions in Perovskite-Type LaScO₃. Inorganic Chemistry, 2018, 57, 8718-8721.	1.9	20
9	Photoluminescence excitation spectra of lanthanide doped YAlO 3 in vacuum ultraviolet region. Optical Materials, 2017, 66, 327-331.	1.7	15
10	Thermoelectric properties and figure of merit of perovskite-type Sr1â^'xLaxSnO3 ceramics. Ceramics International, 2017, 43, 9653-9657.	2.3	5
11	Luminescence and Valence of Tb Ions in Alkaline Earth Stannates and Zirconates Examined by X-ray Absorption Fine Structures. Inorganic Chemistry, 2017, 56, 12625-12630.	1.9	21
12	Transparent Conductive Oxides. Springer Handbooks, 2017, , 1-1.	0.3	17
13	Photo- and cathodoluminescence of Eu3+ or Tb3+ doped CaZrO3 films prepared by pulsed laser deposition. Optical Materials, 2017, 73, 504-508.	1.7	15
14	Phase formation and UV luminescence of Gd3+ doped perovskite-type YScO3. Journal of Solid State Chemistry, 2016, 242, 170-174.	1.4	18
15	Determination of 4f energy levels for trivalent lanthanide ions in YAlO3 by X-ray photoelectron spectroscopy. Thin Solid Films, 2016, 614, 69-72.	0.8	6
16	UV cathodoluminescence of Gd³⁺doped and Gd³⁺ï£¿Pr³⁺co-doped YAlO₃epitaxial thin films. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 703-706.	0.8	14
17	Lanthanide 4f energy levels in perovskite-type YAlO3. Journal of Luminescence, 2015, 168, 14-19.	1.5	10
18	UV emissions in Gd3+ doped or Gd3+â€“Pr3+ Co-doped IIIâ€“III perovskite-type RMO3 (R=Y, La; M=Al, Ga). Thin Solid Films, 2014, 559, 23-26.	0.8	12

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19	Preparation of thin films of perovskite-type YAlO 3 :Gd 3+ â€“Pr 3+ UV phosphors. Thin Solid Films, 2014, 571, 90-93.	0.8	12
20	UV emission from Gd3+ ions in Gd3+â€“Pr3+ codoped YAlO3 perovskite. Journal of Luminescence, 2013, 141, 44-47.	1.5	19
21	Thermoelectric properties and figure of merit of perovskite-type Ba1â^'xLaxSnO3 with x=0.002â€“0.008. Solid State Communications, 2013, 172, 49-53.	0.9	28
22	Optical and electrical properties of heat-resistant Sb-doped Sn1â^'xHfxO2 transparent conducting films. Thin Solid Films, 2012, 520, 3755-3759.	0.8	2
23	Synthesis of Pr3+ doped or Tb3+â€“Mg codoped CaSnO3 perovskite phosphor by the polymerized complex method. Journal of Sol-Gel Science and Technology, 2012, 61, 362-366.	1.1	21
24	Thermoelectric Properties of P -Type BaSnO3 Ceramics Doped with Cobalt. Funtai Oyobi Fummatsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy, 2011, 58, 149-154.	0.1	4
25	High-temperature thermoelectric properties of La-doped BaSnO3 ceramics. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 29-32.	1.7	44
26	Fabrication of Tbâ€“Mg codoped CaSnO3 perovskite thin films and electroluminescence devices. Thin Solid Films, 2010, 518, 3063-3066.	0.8	28
27	Origin of highâ€density hole doping and anisotropic hole transport in a wide gap layered semiconductor LaCuOSe studied by firstâ€principles calculations. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1636-1641.	0.8	8
28	Lowâ€Drivingâ€Voltage Electroluminescence in Perovskite Films. Advanced Materials, 2009, 21, 3699-3702.	11.1	98
29	Tricolor luminescence in rare earth doped CaZrO3 perovskite oxides. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 161, 100-103.	1.7	56
30	Layered mixed-anion compounds: Epitaxial growth, active function exploration, and device application. Journal of the European Ceramic Society, 2009, 29, 245-253.	2.8	21
31	High-Temperature Thermoelectric Properties of La-Doped Ba1-xSrxSnO3 Ceramics. Funtai Oyobi Fummatsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy, 2009, 56, 555-560.	0.1	1
32	Photoluminescence properties of Pr doped and Tbâ€“Mg codoped CaSnO3 with perovskite structure. Thin Solid Films, 2008, 516, 5885-5889.	0.8	41
33	Single crystal growth of LaCuOS by the flux method. Journal of Crystal Growth, 2008, 311, 114-117.	0.7	15
34	Crystal Structures, Optoelectronic Properties, and Electronic Structures of Layered Oxychalcogenides MCuOCh (M = Bi, La; Ch = S, Se, Te): Effects of Electronic Configurations of M³⁺ Ions. Chemistry of Materials, 2008, 20, 326-334.	3.2	258
35	Photoluminescence from Epitaxial Films of Perovskite-type Alkaline-earth Stannates. Applied Physics Express, 2008, 1, 015003.	1.1	29
36	Optoelectronic properties and electronic structure of YCuOSe. Journal of Applied Physics, 2007, 102, 113714.	1.1	19

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37	Heavy hole doping of epitaxial thin films of a wide gap p-type semiconductor, LaCuOSe, and analysis of the effective mass. Applied Physics Letters, 2007, 91, .	1.5	91
38	Blue photoluminescence in Ti-doped alkaline-earth stannates. Journal of Solid State Chemistry, 2007, 180, 1410-1413.	1.4	68
39	Red photoluminescence in praseodymium-doped titanate perovskite films epitaxially grown by pulsed laser deposition. Applied Physics Letters, 2006, 89, 261915.	1.5	45
40	Opto-electronic properties and light-emitting device application of widegap layered oxychalcogenides: LaCuOCh(Ch= chalcogen) and La2CdO2Se2. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 2800-2811.	0.8	50
41	Wide-gap layered oxychalcogenide semiconductors: Materials, electronic structures and optoelectronic properties. Thin Solid Films, 2006, 496, 8-15.	0.8	86
42	Green, Orange, and Magenta Luminescence in Strontium Stannates with Perovskite-Related Structures. Japanese Journal of Applied Physics, 2006, 45, 6981-6983.	0.8	57
43	Electrical and Photonic Functions Originating from Low-Dimensional Structures in Wide-Gap Semiconductors LnCuOCh (Ln=lanthanide, Ch=chalcogen): A Review. Journal of the Ceramic Society of Japan, 2005, 113, 10-16.	1.3	24
44	Excitonic properties related to valence band levels split by spinâ€“orbit interaction in layered oxychalcogenide LaCuOCh(Ch=S,Se). Journal of Luminescence, 2005, 112, 66-70.	1.5	14
45	Electrical Properties and Structure of p-Type Amorphous Oxide SemiconductorxZnOÂ·Rh2O3. Advanced Functional Materials, 2005, 15, 968-974.	7.8	58
46	Optical Properties and Two-Dimensional Electronic Structure in Wide-Gap Layered Oxychalcogenide: La2CdO2Se2.. ChemInform, 2005, 36, no.	0.1	0
47	Electrical and Photonic Functions Originating from Low-Dimensional Structures in Wide-Gap Semiconductors LnCuOCh (Ln: Lanthanide, Ch: Chalcogen): A Review. ChemInform, 2005, 36, no.	0.1	0
48	Two-dimensional electronic structure and multiple excitonic states in layered oxychalcogenide semiconductors, LaCuOCh (Ch=S, Se, Te): Optical properties and relativistic ab initio study. Thin Solid Films, 2005, 486, 98-103.	0.8	21
49	Thermoelectric properties of delafossite-type layered oxides AgIn1â^'xSnxO2. Journal of Applied Physics, 2005, 98, 013706.	1.1	13
50	Valence-band structures of layered oxychalcogenides, LaCuOCh (Ch=S, Se, and Te), studied by ultraviolet photoemission spectroscopy and energy-band calculations. Journal of Applied Physics, 2005, 98, 043506.	1.1	39
51	Excitonic blue luminescence from p-LaCuOSeâ^•n-InGaZn5O8 light-emitting diode at room temperature. Applied Physics Letters, 2005, 87, 211107.	1.5	53
52	Field-Induced Current Modulation in Nanoporous Semiconductor, Electron-Doped 12CaOÂ·7Al2O3. Chemistry of Materials, 2005, 17, 6311-6316.	3.2	45
53	Li-Doped NiO Epitaxial Thin Film with Atomically Flat Surface. Journal of Materials Research, 2004, 19, 913-920.	1.2	32
54	Growth mechanism for single-crystalline thin film of InGaO3(ZnO)5 by reactive solid-phase epitaxy. Journal of Applied Physics, 2004, 95, 5532-5539.	1.1	58

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55	Third-order optical nonlinearity originating from room-temperature exciton in layered compounds LaCuOS and LaCuOSe. Applied Physics Letters, 2004, 84, 879-881.	1.5	56
56	Two-Dimensional Electronic Structures in Layered Oxychalcogenide Semiconductors, LaCuOCh (Ch=S,) Tj ETQq0 0 0 rgBT /Overlock 10	0.1	2
57	Carrier transport of extended and localized states in InGaO3(ZnO)5. Materials Research Society Symposia Proceedings, 2004, 811, 90.	0.1	0
58	Energy band structure of LaCuOCh (Ch = S, Se and Te) calculated by the full-potential linearized augmented plane-wave method. Journal of Physics Condensed Matter, 2004, 16, 5179-5186.	0.7	65
59	Electrical properties and local structure ofn-type conducting amorphous indium sulphide. Philosophical Magazine Letters, 2004, 84, 665-671.	0.5	16
60	All oxide transparent MISFET using high-k dielectrics gates. Microelectronic Engineering, 2004, 72, 294-298.	1.1	22
61	Mechanism for Heteroepitaxial Growth of Transparent P-Type Semiconductor:â€‰ LaCuOS by Reactive Solid-Phase Epitaxy. Crystal Growth and Design, 2004, 4, 301-307.	1.4	54
62	Optical Properties and Two-Dimensional Electronic Structure in Wide-Gap Layered Oxychalcogenide:â€‰ La2CdO2Se2. Journal of Physical Chemistry B, 2004, 108, 17344-17351.	1.2	33
63	Natural nanostructures in ionic semiconductors. Microelectronic Engineering, 2004, 73-74, 620-626.	1.1	17
64	Fabrication of heteroepitaxial thin films of layered oxychalcogenides LnCuOCh (Ln = Laâ€“Nd; Ch =) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 5	1.2	31
65	Carrier transport in transparent oxide semiconductor with intrinsic structural randomness probed using single-crystalline InGaO3(ZnO)5 films. Applied Physics Letters, 2004, 85, 1993-1995.	1.5	247
66	Single-atomic-layered quantum wells built in wide-gap semiconductorsLnCuOCh(Ln=lanthanide,Ch=chalcogen). Physical Review B, 2004, 69, .	1.1	97
67	Thermoelectric properties of layered oxyselenides La1â^'xSrxCuOSe (x=0 to 0.2). Journal of Applied Physics, 2004, 95, 3594-3597.	1.1	39
68	Synthesis of single-phase layered oxychalcogenide La2CdO2Se2: crystal structure, optical and electrical properties. Journal of Materials Chemistry, 2004, 14, 2946.	6.7	35
69	Quantum beat between two excitonic levels split by spinâ€“orbit interactions in the oxychalcogenide LaCuOS. Optics Letters, 2004, 29, 1659.	1.7	17
70	Single-Crystalline Films of the Homologous Series InGaO3(ZnO)m Grown by Reactive Solid-Phase Epitaxy. Advanced Functional Materials, 2003, 13, 139-144.	7.8	179
71	A p-Type Amorphous Oxide Semiconductor and Room Temperature Fabrication of Amorphous Oxide pâ€“n Heterojunction Diodes. Advanced Materials, 2003, 15, 1409-1413.	11.1	154
72	Electron transport in InGaO3(ZnO)m (m=integer) studied using single-crystalline thin films and transparent MISFETs. Thin Solid Films, 2003, 445, 322-326.	0.8	11

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73	Preparation and crystal structure analysis of CeCuOS. Journal of Solid State Chemistry, 2003, 170, 182-187.	1.4	46
74	Wide gap p-type degenerate semiconductor: Mg-doped LaCuOSe. Thin Solid Films, 2003, 445, 304-308.	0.8	41
75	Frontier of transparent oxide semiconductors. Solid-State Electronics, 2003, 47, 2261-2267.	0.8	129
76	Electrical and Optical Properties and Electronic Structures of LnCuOS (Ln = Laâˆ¼Nd). Chemistry of Materials, 2003, 15, 3692-3695.	3.2	94
77	Thin-Film Transistor Fabricated in Single-Crystalline Transparent Oxide Semiconductor. Science, 2003, 300, 1269-1272.	6.0	1,709
78	Intrinsic excitonic photoluminescence and band-gap engineering of wide-gapp-type oxychalcogenide epitaxial films of LnCuOCh (Ln=La, Pr, and Nd; Ch=S or Se) semiconductor alloys. Journal of Applied Physics, 2003, 94, 5805-5808.	1.1	79
79	Degenerate p-type conductivity in wide-gap LaCuOS1âˆ'xSex (x=0â€“1) epitaxial films. Applied Physics Letters, 2003, 82, 1048-1050.	1.5	166
80	Electrical conductivity control in transparent p-type (LaO)CuS thin films prepared by rf sputtering. Journal of Applied Physics, 2002, 91, 9177-9181.	1.1	65
81	Carrier doping into MgIn2O4 epitaxial thin films by proton implantation. Journal of Applied Physics, 2002, 91, 2112-2117.	1.1	7
82	Heteroepitaxial growth of a wide-gap p-type semiconductor, LaCuOS. Applied Physics Letters, 2002, 81, 598-600.	1.5	105
83	Carrier generation in highly oriented WO3 films by proton or helium implantation. Journal of Applied Physics, 2002, 92, 2017-2022.	1.1	27
84	EPITAXIAL GROWTH OF TRANSPARENT CONDUCTIVE OXIDES. International Journal of Modern Physics B, 2002, 16, 173-180.	1.0	15
85	Wide-gap P-type Conductive Properties in Layered Oxychalcogenides. Materials Research Society Symposia Proceedings, 2002, 747, 1.	0.1	0
86	X-ray Amorphous P-type Conductive Oxide; ZnRh2O4. Materials Research Society Symposia Proceedings, 2002, 747, 1.	0.1	2
87	Heteroepitaxial Growth of a Wide Gap P-type Oxysulfide, LaCuOS. Materials Research Society Symposia Proceedings, 2002, 747, 1.	0.1	0
88	ZnRh2O4: A p-type semiconducting oxide with a valence band composed of a low spin state of Rh3+ in a 4d6 configuration. Applied Physics Letters, 2002, 80, 1207-1209.	1.5	105
89	Electronic Structure of Sr2Cu2ZnO2S2Layered Oxysulfide with CuS Layers. Chemistry of Materials, 2002, 14, 1037-1041.	3.2	36
90	Electronic structure and optical properties of SrCu2O2. Journal of Applied Physics, 2002, 91, 3074-3078.	1.1	66

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91	Band gap engineering, band edge emission, and p-type conductivity in wide-gap LaCuOS1â˜'xSex oxychalcogenides. Journal of Applied Physics, 2002, 91, 4768-4770.	1.1	102
92	Decomposition of water by a CaTiO3 photocatalyst under UV light irradiation. Materials Research Bulletin, 2002, 37, 2401-2406.	2.7	112
93	Preparation of transparent p-type (La1â˜'xSrxO)CuS thin films by r.f. sputtering technique. Thin Solid Films, 2002, 411, 125-128.	0.8	77
94	Frontier of transparent conductive oxide thin films. Vacuum, 2002, 66, 419-425.	1.6	164
95	Crystal structure of LaCuOS1â˜'xSex oxychalcogenides. Thin Solid Films, 2002, 411, 115-118.	0.8	44
96	Novel film growth technique of single crystalline In2O3(ZnO)m (m=integer) homologous compound. Thin Solid Films, 2002, 411, 147-151.	0.8	39
97	Epitaxial growth of transparent p-type conducting CuGaO[sub 2] thin films on sapphire (001) substrates by pulsed laser deposition. Journal of Applied Physics, 2001, 89, 1790.	1.1	390
98	Electronic structure of the transparentp-type semiconductor (LaO)CuS. Physical Review B, 2001, 64, .	1.1	114
99	Electrical and Optical Properties of Layered Oxysulfides with CuS Layers: Srâ˜'Cuâ˜'Mâ˜'Oâ˜'S System (M =) Tj ETQq1 1 0.784314 rgBT	3.2	41
100	Bipolar Electrical Conductive Transparent Oxide, CuInO2. Materials Research Society Symposia Proceedings, 2001, 666, 3141.	0.1	0
101	Transparent P-type Conducting LaCuOS Layered Oxysulfide. Materials Research Society Symposia Proceedings, 2001, 666, 271.	0.1	0
102	Fabrication of all oxide transparent pâ€"n homojunction using bipolar CuInO2 semiconducting oxide with delafossite structure. Solid State Communications, 2001, 121, 15-17.	0.9	134
103	Bipolarity in electrical conduction of transparent oxide semiconductor CuInO2 with delafossite structure. Applied Physics Letters, 2001, 78, 1583-1585.	1.5	332
104	Room-temperature excitons in wide-gap layered-oxysulfide semiconductor: LaCuOS. Applied Physics Letters, 2001, 78, 2333-2335.	1.5	133
105	Transparent p- and n-Type Conductive Oxides With Delafossite Structure. Materials Research Society Symposia Proceedings, 2000, 623, 235.	0.1	8
106	Crystal structure of metastable Î²-CeZrO4 phase possessing an ordered arrangement of Ce and Zr ions. Journal of Alloys and Compounds, 2000, 312, 94-103.	2.8	124
107	Transparent p-Type Conducting Oxides: Design and Fabrication of p-n Heterojunctions. MRS Bulletin, 2000, 25, 28-36.	1.7	530
108	Preparation of n-type conductive transparent thin films of AgInO2:Sn with delafossite-type structure by pulsed laser deposition. Journal of Applied Physics, 2000, 88, 3067-3069.	1.1	27

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109	Electronic Structure of SrNb8O14 and Mg3Nb6O11 Studied by Spectroscopic Methods. Chemistry of Materials, 2000, 12, 2659-2663.	3.2	0
110	Electronic structure and optoelectronic properties of transparent p-type conducting CuAlO[sub 2]. Journal of Applied Physics, 2000, 88, 4159.	1.1	413
111	Study on electronic structure of CaTiO3by spectroscopic measurements and energy band calculations. Journal of Physics Condensed Matter, 1999, 11, 3535-3545.	0.7	34
112	Fabrication of transparent pâ€“n heterojunction thin film diodes based entirely on oxide semiconductors. Applied Physics Letters, 1999, 75, 2851-2853.	1.5	194
113	Transparent Conducting Oxides Based on the Spinel Structure. Journal of the American Ceramic Society, 1999, 82, 3330-3336.	1.9	115
114	n-type electrical conduction in transparent thin films of delafossite-type AgInO2. Applied Physics Letters, 1998, 72, 1036-1038.	1.5	73
115	Vacuum ultraviolet reflectance and electron energy loss spectra of. Journal of Physics Condensed Matter, 1998, 10, 3669-3677.	0.7	58
116	Electrical and magnetic properties of hole-dopedSr1+xLa1â^'xFeO4. Physical Review B, 1994, 49, 10194-10199.	1.1	28
117	Electronic structure of hole-dopedSr1+xLa1â^'xFeO4studied by UPS and XAS. Physical Review B, 1994, 49, 10200-10205.	1.1	9
118	New ultravioletâ€transport electroconductive oxide, ZnGa2O4spinel. Applied Physics Letters, 1994, 64, 1077-1078.	1.5	214
119	New oxide phase with wide band gap and high electroconductivity CdGa2O4spinel. Applied Physics Letters, 1993, 62, 499-500.	1.5	79
120	Synthesis of Pb(Mg_{1/3}Nb_{2/3})O₃ Powder by the Spray Pyrolysis with Ultrasonic Atomizer. Journal of the Ceramic Society of Japan, 1992, 100, 246-249.	1.3	15
121	New oxide phase with wide band gap and high electroconductivity, MgIn2O4. Applied Physics Letters, 1992, 61, 1954-1955.	1.5	128
122	Energy Diagrams of Lanthanide Energy Levels in Perovskiteâ€Type Calciumâ€Based Double Oxides Examined by Xâ€ray Photoelectron Spectroscopy. Physica Status Solidi (B): Basic Research, 0, , 2100450.	0.7	2